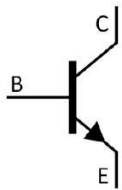


TO-92LM NPN Silicon NPN transistor in a TO-92LM Plastic Package.

2SA966 3W
 Complementary to 2SA966 And 3 watts output applications.

Audio frequency power amplifier applications.

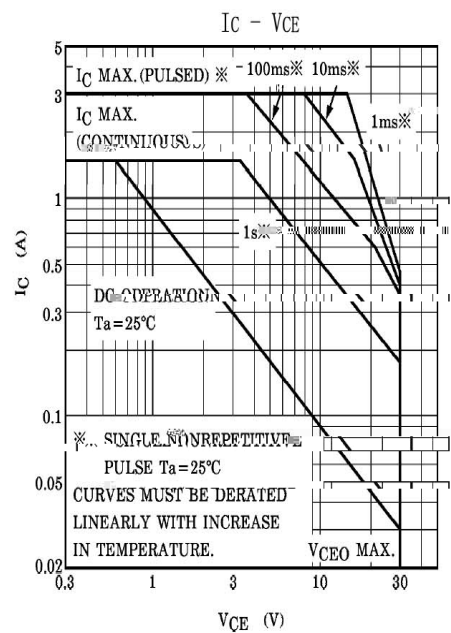
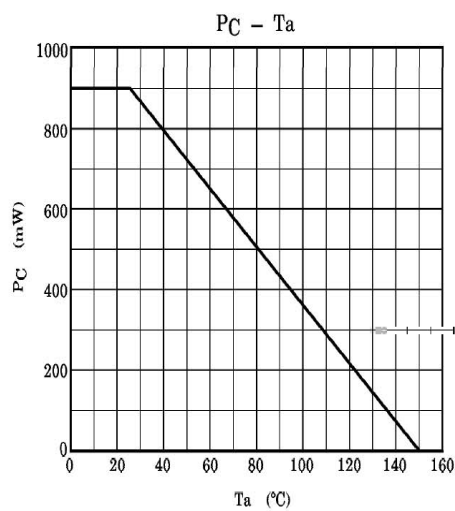
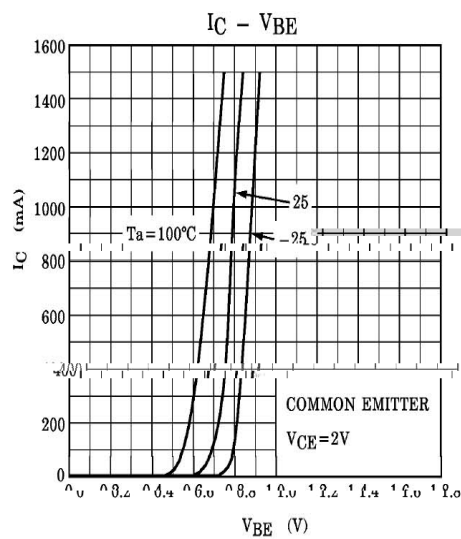
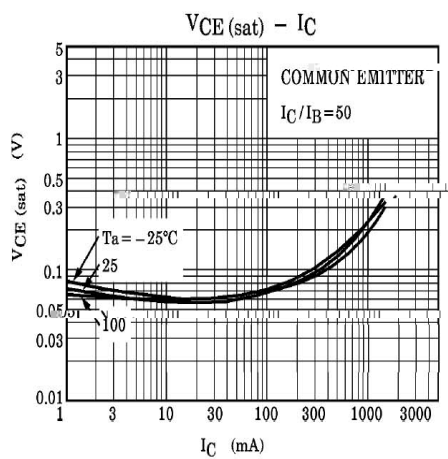
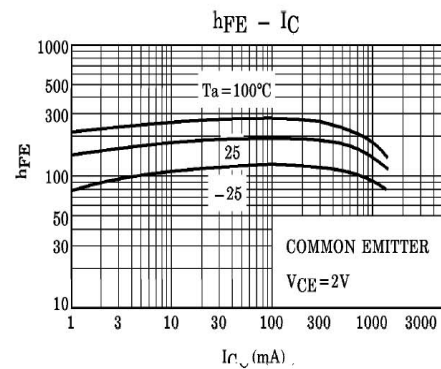
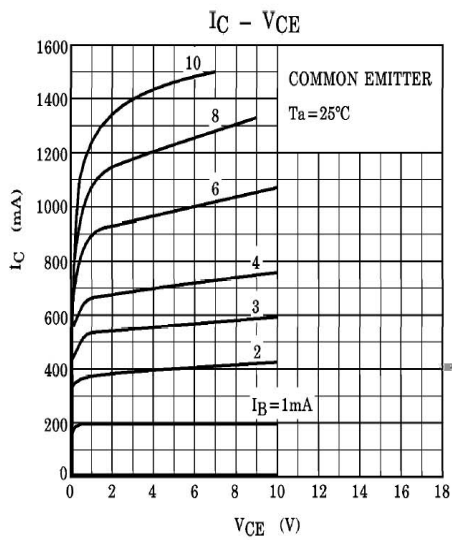


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320

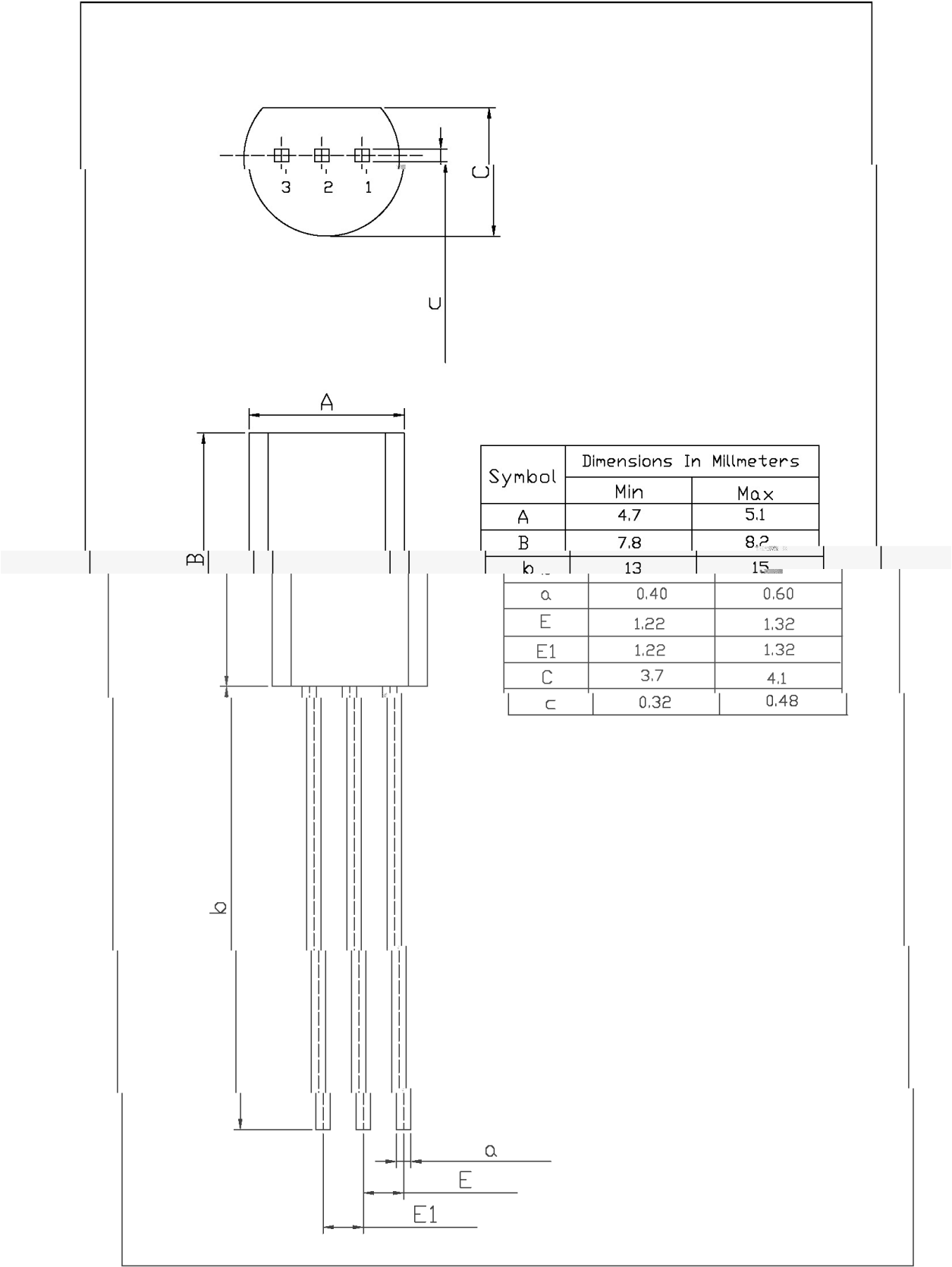
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	1.5	A
Emitter Current	I_E	-1.5	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

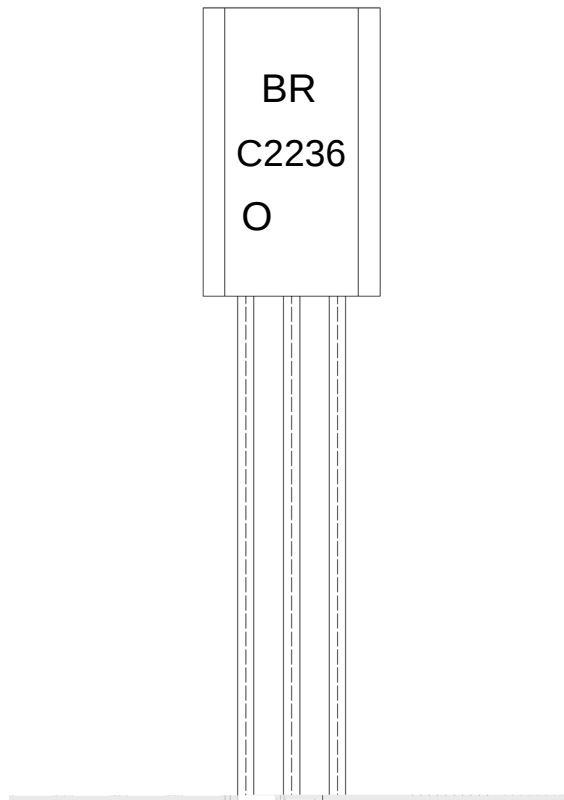
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=1.0mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=30V$ $I_E=0$			0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	A
DC Current Gain	h_{FE}	$V_{CE}=2.0V$ $I_C=500mA$	100		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A$ $I_B=0.03A$			2.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=2.0V$ $I_C=500mA$			1.0	V
Transition Frequency	f_T	$V_{CE}=2.0V$ $I_C=500mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$			30	pF



T0-92LM

Unit: mm





BR:

C2236

O: h_{FE}

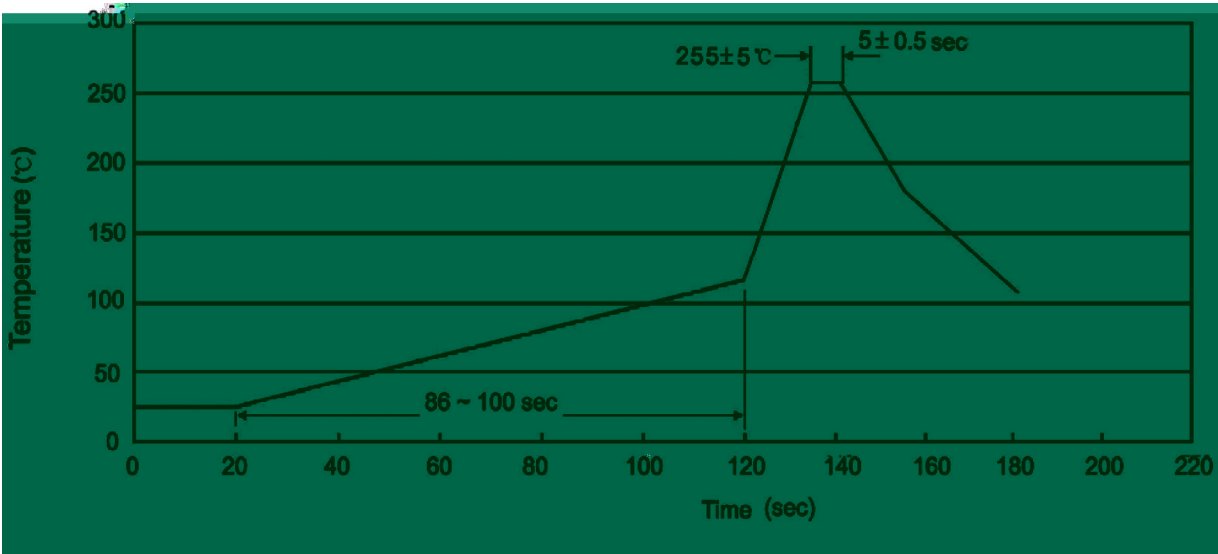
Note:

BR: Company Code.

C2236: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension		(unit mm3)